

isc Silicon PNP Power Transistor

BD736

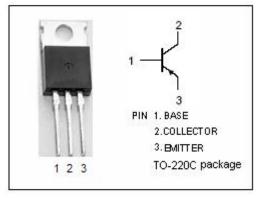
DESCRIPTION

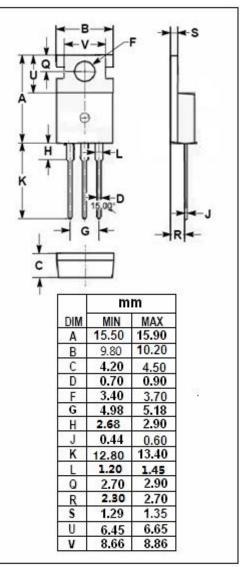
- DC Current Gain -
 - : h_{FE} = 40(Min.)@ I_C= -20mA
- Collector-Emitter Breakdown Voltage-
 - : V_{(BR)CEO}= -35V(Min.)
- Complement to Type BD735
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

APPLICATIONS

· Designed for amplifier and switching applications.

| ABSOLUTE MAXIMUM RATINGS(Ta=25℃) | | | | | | |
|----------------------------------|---|---------|------|--|--|--|
| SYMBOL | PARAMETER | VALUE | UNIT | | | |
| V _{CBO} | Collector-Base Voltage | -35 | V | | | |
| V _{CEO} | Collector-Emitter Voltage | -35 | V | | | |
| V _{EBO} | Emitter-Base Voltage -5 | | V | | | |
| lc | Collector Current-Continuous | -4 | А | | | |
| I _{CM} | Collector Current-Peak | -7 | А | | | |
| I _B | Base Current-Continuous | -1 | A | | | |
| Pc | Collector Power Dissipation @ Ta=25°C | 2 | W | | | |
| | Collector Power Dissipation @ $T_c=25^{\circ}C$ | 40 | | | | |
| TJ | Junction Temperature | 150 | °C | | | |
| T _{stg} | Storage Temperature Range | -55~150 | °C | | | |
| | | | | | | |





isc website: www.iscsemi.com



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ELECTRICAL CHARACTERISTICS

$T_{c}\text{=}25^{\circ}\!\!\!\mathrm{C}$ unless otherwise specified

| SYMBOL | PARAMETER | CONDITIONS | MIN | МАХ | UNIT |
|----------------------|--------------------------------------|---|-----|------|------|
| V _{(BR)CEO} | Collector-Emitter Breakdown Voltage | I _C = -30mA; I _B = 0 | -35 | | V |
| V _{(BR)CBO} | Collector-Base Breakdown Voltage | I _C = -0.1mA; I _E = 0 | -35 | | V |
| V _{(BR)EBO} | Emitter-Base Breakdown Voltage | I _E = -1mA; I _C = 0 | -5 | | V |
| V _{CE(sat)} | Collector-Emitter Saturation Voltage | I _C = -2A; I _B = -0.2A | | -0.6 | V |
| $V_{\text{BE(on)}}$ | Base-Emitter On Voltage | I _C = -2A; V _{CE} = -1V | | -1.1 | V |
| I _{CES} | Collector Cutoff Current | V _{CE} = -35V; V _{BE} = 0 | | -0.2 | mA |
| h _{FE-1} | DC Current Gain | I _C = -20mA; V _{CE} = -4V | 40 | | |
| h _{FE-2} | DC Current Gain | I _C = -2A; V _{CE} = -1V | 40 | | |

NOTICE:

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